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March 15, 2024

Analytical Chemistry

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The NanoSIMS-HR: the next generation of high spatial resolution dynamic SIMS

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Cite as:

P. K. Weber, M. Debliqui, C. Defouilloy, X. Mayali, M.-C. Liu, R. Hestrin, J. Pett-Ridge, R. Stuart, M. Morris, C. Ramon, D. M. Jorgens, R. Zalpuri, L. Arnoldi, J. Farcy, N. Saquet, S. Vitcher Fichou, L. Renaud, A. Thomen (2024) The NanoSIMS-HR: the next generation of high spatial resolution dynamic SIMS. *Analytical Chemistry* 96, 49, 19321–19329. <https://doi.org/10.1021/acs.analchem.4c03091>

LLNL-JRNL-861788

Abstract

The high lateral resolution and sensitivity of the NanoSIMS 50 and 50L series of dynamic SIMS instruments has enabled numerous scientific advances over the past 25 years. Here we report on the NanoSIMS-HR, the first major upgrade to the series, and analytical tests in a suite of sample types, including an aluminum sample containing silicon crystals, microalgae and plant roots colonized with arbuscular mycorrhizal fungi. Significant improvements have been made in the Cs⁺ ion source, high voltage (HV) control, stage reproducibility, and other aspects of the instrument that affect performance. The modified design of the NanoSIMS-HR thermal-ionization Cs⁺ source enables a 5-pA primary ion beam to be focused into a 100 nm spot, a ~2.5-fold increase compared to Cs⁺ sources on previous instruments (~2 pA at 100 nm). The brightness of the new Cs⁺ source enables an ultimate lateral resolution as high as 30 nm and improved detection limits for a given analysis area. Sample stage movement accuracy is higher than 500 nm, enabling many-fold higher throughput automated analyses. With the new HV control, the primary ion beam impact energy can be reduced from 16 keV to 2 keV, which enables higher depth resolution during depth profiling (a 2-fold improvement), albeit with a 5-fold decrease in lateral resolution. In the NanoSIMS-HR, the secondary ion column and detection system are identical to those used in the previous series, and isotopic analysis performance is as precise as in previous NanoSIMS instruments.

Introduction

Secondary ion mass spectrometry (SIMS) is a spatially resolved analytical method for characterizing solid samples. First invented in the 1960s^{1,2}, SIMS instruments have been developed along multiple lines of emphasis, with the class of magnetic sector “dynamic SIMS” instruments emphasizing high-sensitivity elemental and isotopic analyses³. In the 1990s, Georges Slodzian, the inventor of SIMS, conceptualized a coaxial design that enabled dynamic SIMS with higher lateral resolution by improving the primary ion beam focusing for scanning ion imaging^{4,5}. Further developed by Francois Hillion and others, that design became the basis for the NanoSIMS 50 series of instruments⁶. The key capabilities of these instruments are high mass resolving power ($>9000 M/\Delta M$) with high transmission (up to 25%) at high-lateral resolution (as good as 50 nm)⁷. Five (NanoSIMS 50) or seven (NanoSIMS 50L) detectors can also be positioned for simultaneous detection to increase the fraction of ions detected from the sampled volume.

The NanoSIMS 50 series capabilities translate to high mass specificity and sensitivity for the analysis of small features and have enabled discoveries in fields as diverse as cosmochemistry, geology, soil science, structural biology, biomedical research, microbial ecology, and material science⁸⁻¹². Inspired by these successes, the scientific and analytical communities have sought improvements to the NanoSIMS 50 series to further improve spatial resolution, analytical performance and throughput.

50 nanometer lateral resolution has been a featured aspect of the NanoSIMS instruments. NanoSIMS instruments use a normal-incidence primary ion beam with a 16 keV impact energy to sputter the sample to generate secondary ions for analysis⁶. At this energy, the primary ion beam can be finely focused for scanning secondary ion imaging. However, to achieve 50 nm lateral resolution, the primary current must be reduced by $\sim 10\times$ over typical operating conditions for biological samples (Mayali et al. 2023) increasing the analysis time proportionally.

Primary ion source intensity (“brightness”) is a factor controlling in the relationship between primary ion beam spot size and current¹³, and multiple efforts have been made to increase both the positive cesium ion source—used to enhance the yield of negative secondary ions^{14,15}, and the negative oxygen ion source—used to enhance the yield of positive secondary ions^{13,16}. Increased ion source brightness would improve the lateral resolution of NanoSIMS instruments, allowing smaller features—from viruses to presolar grains—to be resolved.

Increased source brightness would also allow higher beam current analyses for lower resolution spot sizes, with the benefits of faster analyses, reduced ion counts from gas phase contribution, and fewer detector dark counts, thereby reducing limits of detection³.

Increased source brightness could also be leveraged to increase the depth resolution of NanoSIMS analyses while maintaining high lateral resolution. Depth profiling—the practice of using the primary ion beam to erode through the sample while collecting compositional data—is a standard SIMS method that can achieve a few nanometer depth resolution³. By comparison, the depth resolution of the NanoSIMS series of instruments is on the order of 10s of nanometers because the normal incident 16 keV primary ion beam penetrates into the sample to depths >20 nm¹⁷. Depth resolution could be improved by lowering the primary ion beam impact energy, but at the cost of lower lateral resolution. Higher source brightness would regain some of the loss in lateral resolution, which would allow depth profiling of

features that cannot be resolved with standard SIMS instruments, such as thin film transistors and attached bacteria.

While NanoSIMS data can be quantitated to the extent that standards and good analytical and statistical practices are used, the small scale of the analyses (typically less than $50 \times 50 \mu\text{m}^2$) can present challenges with translating the results to the population scale. This issue is often encountered in microbial ecology studies, where single cell incorporation of an isotopically labeled substrate can vary by over 10x among cells¹⁸ and some cell types can be relatively rare, such as non-cyanobacterial nitrogen fixing bacteria in the open ocean¹⁹. As a result, there is demand for automation and high throughput to increase data set sizes to collect representative samples. Cosmochemistry and other fields have similar needs. As discussed above, a higher brightness primary ion source is one potential route for increasing throughput. Other factors include stage reproducibility and navigation.

Here we test a new NanoSIMS-HR instrument for lateral resolution, depth resolution, limits of detection, stage reproducibility, and isotopic ratio reproducibility. Lateral resolution measurements were conducted on an aluminum sample containing silicon crystals, and representative images were collected for (1) microalgae and (2) plant roots colonized with arbuscular mycorrhizal fungi. Depth resolution measurements were conducted on a delta layer sample at 16, 8, and 4 keV impact energy. Limit of detection measurements were made on a phosphorus implant. Isotopic ratio data were collected on a Si wafer and a quartz standard.

Experimental Section

Instrument: The NanoSIMS-HR, like its predecessors the NanoSIMS 50 and 50L, is a scanning ion microprobe coupled to a double-focusing mass spectrometer with a Mattauch-Herzog design, which enables multicollection of secondary ions over a large relative mass range ($\sim 22\times$ for the 50L)^{4-6, 20}. The primary ions are accelerated toward the sample surface and steered and focused to the desired spot size by a suite of Einzel lenses and deflectors. To optimize focusing, the instrument is designed so that the primary and secondary ions travel in opposite directions through a single “coaxial” lens stack near the sample. As a result, the primary ion source and the sample surface must be at the same potential and opposite polarity. Normal operation is with the source and sample at $|8000\text{V}|$, resulting in a primary ion impact energy of 16 keV. The NanoSIMS-HR multicollection system has seven detectors, six of which are on movable trolleys to enable mass selection. Electron multiplier (EM) ion detectors in pulse counting mode are used to enable imaging; these can be swapped for Faraday cups (FC) for high-current, higher-precision isotope measurements. Relative to its predecessor instruments, the NanoSIMS-HR includes several key upgrades:

Upgraded item 1: The ionizer, extraction optics and reservoir of the thermal Cs^+ primary ion source were redesigned to optimize the angular intensity of the Cs^+ beam, improving brightness. For operations in positive polarity, the NanoSIMS-HR has the same radio frequency plasma O^- source²¹ included with the NanoSIMS 50L; analyses using that source are not included herein.

Upgraded item 2: The HV boards and electronics were redesigned to allow the primary ion source and sample to be changed to enable low-impact energy analyses. The range of operation is from the standard 16 keV impact energy to 2 keV.

Upgraded item 3: The analysis chamber sample stage has been upgraded to include a position encoder from Horiba Scientific. This sample stage enables sample navigation over a 50 x 50 mm² sample holder, as well as between SIMS analysis, optical imaging and primary ion beam measurement positions, requiring up to 100 mm in movement. To increase point reproducibility, the stage is equipped with an encoded plate used as a coordinate reference. An optical microscope equipped with a camera monitors the encoded plate to determine the absolute coordinates of the sample holder.

In addition, we note here that the NanoSIMS-HR includes navigation upgrades related to the fact that the sample cannot be observed with an optical system while in the SIMS position because the coaxial lens is too close. As a result, to navigate the sample with optical imaging, the sample holder is moved approximately 40 mm to position the sample in front of an optical objective. In the NanoSIMS-HR, the optical system has been improved to allow approximately ≤ 1 -micron lateral resolution light imaging and mosaic image collection co-registered with the ion beam for SIMS-mode navigation.

Lateral resolution analyses

To compare lateral resolution of the NanoSIMS-HR to a NanoSIMS 50L, measurements were made on an aluminum sample with high silicon content (“Al-Si sample”) because the Si forms Al-free domains that provide sharp chemical contrast for these measurements. The sample was polished with diamond paste down to 0.1 micron (Buehler) and then colloidal silica (Buehler). Additional imaging was performed with biological samples, detailed below.

Lateral resolution was determined for a range of primary Cs⁺ beam currents (~0.2 pA to 600 pA) and impact energies (16 keV to 2 keV). Primary ion current selection and focusing was performed as is typical for NanoSIMS instruments. Ion currents were controlled using Einzel lenses (L0 and L1) and a primary beam limiting aperture (D1) located in the coaxial optics column, astigmatism was corrected with an octopole, and the final focusing of the primary beam onto the sample surface was performed with EOP, a lens in the coaxial lens stack. The impact energy was adjusted by sweeping the potential of the source tube containing the Cs reservoir and adjusting the sample potential to the optimized value. High voltages on the lenses and deflectors in between for primary and secondary optics were scaled down with the energy decrease. Imaging was performed with electron multipliers in pulse counting mode and secondary electrons (SE). The mass spectrometer was operated without an entrance or aperture slit (~2000 mass resolving power (MRP)) for the highest lateral resolution (lowest primary beam current) analyses to achieve the most precise beam resolution measurements by optimizing ion transmission. The beam size was measured by imaging an Al-Si sample with ²⁸Si⁻. ²⁷Al¹H⁻ counts at mass 28 were negligible. Image collection parameters were set to provide a beam overlap from 75% for high lateral resolution image to 99% for large beam for NanoSIMS 50L and from 85% to 97n% for NanoSIMS-HR (2 x 2 to 20 x 20 μm² for NanoSIMS-HR and 5 x 5 to 12 x 12 μm² for the NanoSIMS 50L; all with 512 x 512 pixels; beam overlap defined as the [beam diameter - pixel width] ÷ beam diameter x 100%). The dwell time varied from 0.2 to 3 milliseconds per pixel. As the intensity profile across two chemically contrasting phases (Al and Si in this case) is a convolution between the sharp edge and gaussian beam intensity distribution, a cumulative gaussian distribution model was used to describe the ²⁸Si⁻ profile. Beam size was defined as the distance represented by the 16 to 84% quantile of the intensity distribution containing 68% of the beam intensity. Ion count transects across selected features were extracted in WinImage ion image data processing software (CAMECA) using a region of interest (ROI) of 2 to 4 pixels wide line by 1 pixel deep to average adjacent pixels perpendicular. Lateral resolution was calculated in WinCurve data processing

software (CAMECA) using a cumulative Gaussian distribution model to extract 16% and 84% beam intensity locations on the profile abscissa as the beam size or lateral resolution²².

Biological sample imaging

For comparison to the Al-Si measurements, biological samples were imaged with $^{13}\text{C}^{12}\text{C}^-$ and $^{12}\text{C}^{14}\text{N}^-$ secondary ions generated by Cs^+ primary ions.

The microalga *Phaeodactylum tricornutum* (CCMP2561, Bigelow National Center for Marine Algae and Microbiota) was imaged to illustrate the different analysis conditions. The microalga was grown on ^{13}C and ^{15}N labeled inorganic C and N for 48 hours, then fixed with 10% formalin overnight and filtered onto 2 μm pore size polycarbonate membranes and rinsed with double distilled water. Filters were dried overnight at 50°C prior to excising a portion to mount onto a conductive carbon tab (Ted Pella, California, U.S.A.) adhered to an aluminum stub. Mounted samples were sputter coated with ~5 nm of gold.

A thin section of a mycorrhizal root sample was imaged for correlation with transmission electron micrographs. The sample was prepared from the grass *Panicum hallii* infected with the arbuscular mycorrhizal fungus *Rhizophagus irregularis* (formerly *Glomus intraradices*), grown as described in Hestrin et al. (2022). *P. hallii* seeds were germinated on Petri plates, transferred into cones filled with double-autoclaved sand, inoculated with ~500 *R. irregularis* spores, and grown for eight weeks before being transplanted into cones filled with a 50:50 (v:v) mixture of double-autoclaved sand and a fine sandy loam soil collected from a pasture in Caddo County, OK (35.072417/-98.303667). The sand:soil mixture began at 15% moisture and declined to 5% over the course of the 3-month greenhouse experiment. The plants were grown with a 16 hr photoperiod and average daytime and nighttime temperatures of 27 °C and 24 °C, respectively. At harvest, roots were washed, fixed in 50% ethanol, and stored at 4 °C. To prepare samples for imaging, 1-2 mm root segments were excised and transferred to a fresh fixative buffer (2% Tween, 3% glutaraldehyde, 3% paraformaldehyde in 0.05M sodium cacodylate buffer, pH 7.2 (EMS, Hatfield, PA, USA)) and microwaved (Pelco BioWave; Ted Pella, Redding, CA, USA) while under vacuum at room temperature (2×; 1 min 150 W (watts) – hold 1 min – 1 min 150 W – hold 1 min – 1 min 150 W; 27 mbar (20 mm Hg vacuum)). Samples were then held under vacuum for 1 hr and stored overnight at 4 °C. Samples were rinsed (3×; 10 min) in 0.05M sodium cacodylate buffer (pH 7.2) and then immersed in a solution of 1% osmium tetroxide with 1.6% potassium ferricyanide in 0.05M sodium cacodylate buffer and microwaved (2×; 1 min 150 W – hold 1 min; 27 mbar at room temperature). Samples were rinsed in a solution of 0.05M sodium cacodylate buffer, pH 7.2 (3×; 10 min at room temperature) and then subjected to an ascending acetone gradient (10 min; 35%, 50%, 70%, 80%, 90%, 100%) followed by pure acetone (3×; 10 min at room temperature). Samples were progressively infiltrated while rocking with Epon resin and acetone mixtures (EMS, Hatfield, PA, USA). For the final 3 exchanges of 100% Epon resin, samples were microwaved at room temperature (1×; 1 min 250 W – hold 1 min; 27 mbar) and then rocked for 2 hr at each step. Finally, samples were polymerized at 60 °C for 48 hours. Thin sections were cut using a Leica UC6 (Leica, Wetzlar, Germany). A 90 nm thin section was collected onto a formvar-coated copper-rhodium backed slot grid. The grid was post-stained for TEM imaging with 2% uranyl acetate followed by Reynold's lead citrate, for 5 min each. The section was imaged with a Tecnai 12 120-keV TEM (FEI, Hillsboro, OR, USA). Image data were recorded using a Gatan Rio16 CMOS camera with GWS software (Gatan Inc., Pleasanton, CA, USA). TEM sections were then sputter coated with ~5 nm of gold.

Depth resolution analyses

Depth resolution measurements were made using a custom “delta layer” sample consisting of a silicon substrate with thin phosphorus-rich layers of up to 5% P atoms per Si atoms (2.5×10^{21} P at./cm³) laid down by vapor deposition between silicon layers. The P-rich layers were at 30, 90, 180 and 330 nm depth from the surface (ihp-microelectronics.com). Depth profiles were acquired by using a Cs⁺ primary beam from 16 keV to 4 keV at 500 pA and by rastering a $20 \times 20 \mu\text{m}^2$ area. MRP was >9000 at 8 keV of secondary ions energy as reported by the NanoSIMS software (based on peak side slope width from 10% to 90% of peak height; equivalent to ~6000 MRP for peak width at 10% height)²³⁻²⁵. ³¹P⁻ and ³⁰Si⁻ images were acquired with a counting time per frame of 4 s for a total acquisition time of about an hour. Images were processed with WinImage by defining a ROI of $8 \times 8 \mu\text{m}^2$ in the image center to extract the counts rates of phosphorus with minimal ion contributions from the analysis periphery. Profiles were then processed with WinCurve to scale the depth and extract depth resolution. Because P is known to diffuse into the overlying Si during deposition but not into the deeper layer (verified by IMS-7f), depth resolution was based on the rate at which the ³¹P⁻ counts drop off after each layer.

Measurements of P detection limit in Si wafer with Cs⁺ analysis

P detection limits were measured using a P-implanted silicon wafer for a range of Cs⁺ primary currents and raster sizes to determine the minimum detection limit and optimal raster for each primary current setting. The dose of P was 5.48×10^{13} at./cm³ implanted at 200 keV. The peak of the implant was at a depth of 250 nm ($\pm 1\%$), verified by IMS-WF relative to NIST SRM 2133. The NanoSIMS-HR was tuned for >9000 MRP (10%-90% definition) with entrance slit (ES) 4, aperture slit (AS) 3, and a fully open energy slit (EnS) to simultaneously collect ³¹P⁻ and ³⁰Si⁻. The Cs⁺ current on the sample was varied from 10 pA to 8000 pA, and the raster size was varied from $2 \times 2 \mu\text{m}^2$ to $40 \times 40 \mu\text{m}^2$ to test the optimal pairing of primary current and raster size. Depth profiles were collected in imaging mode with 128×128 to 256×256 pixels for 130 to 400 cycles. The data were processed with WinImage to extract depth profiles from ROIs ranging from the full image down to 10% of the imaged area, with the ROI always in the center of the image. Depth profiles were processed with Wincurve. Ion counts were converted to concentration (in P at./cm³) as a function of depth after deriving a relative sensitivity factor based on the known total dose. The apparent P concentration in the background tail of the P profile, where no P is sputtered and background dominates the signal, is defined as the detection limit.

Stage performance

The stage movement reproducibility was measured by moving the stage ~40 mm away from the center location and back and then performing an internal measurement of the shift in subsequent ion images. A standard deviation on shifts in both directions is deemed as an estimation of the reproducibility of the movement. To test this performance, ²⁸Si⁻ ion images were acquired by scanning a $12 \times 12 \mu\text{m}^2$ area defined with 512×512 pixels and a dwell time of 0.3 ms/pixel, and a lateral resolution of 120 nm. An image was acquired in ~80 s in SIMS position, then the sample stage was moved in front of the optical microscope and moved back again in SIMS position for a subsequent image acquisition. This sequence was repeated until a total of 8 images were acquired. WinImage was then used to calculate the shift between 2 consecutive images. An algorithm of image registration with a subpixel precision²² calculated the shifts in x and y directions. The first image was defined as the reference image, and image shifts in both directions were calculated from it.

Isotopic ratio measurements

Multicollection (simultaneous) isotope ratio measurements were made with three different configurations: (1) three Si isotopes ($^{28}\text{Si}^-$, $^{29}\text{Si}^-$ and $^{30}\text{Si}^-$) from silicon wafers (conductor) with ~ 1 pA Cs^+ and $4 \times 4 \mu\text{m}^2$ rasters measured on three EMs, (2) three Si isotopes from the same Si wafers with 600 pA Cs^+ and $10 \times 10 \mu\text{m}^2$ rasters measured on three FCs, (3) oxygen isotopes ($^{16}\text{O}^-$ and $^{18}\text{O}^-$) from a polished Pt-coated quartz substrate (insulator) with 15 nA Cs^+ and $10 \times 10 \mu\text{m}^2$ rasters measured on two FCs. The normal-incidence electron flood gun was used for charge compensation. The NanoSIMS-HR was tuned for >7000 MRP (10%-90% definition). Data were collected in multicollection “isotope mode” with 64×64 pixels. The duration of one analysis, including pre-analysis sputtering, automatic secondary ion beam focusing and centering, automatic mass line centering, and data acquisition, was 10 min, 2 min 30 sec, and 3 min, respectively. Multiple reproducibility tests were conducted, including tests with small (microns), medium (millimeters), and large (10s of millimeters) movements (Table S1; see also Results). Magnet stability was maintained with NMR control.

Results

Lateral Resolution

Lateral resolution as a function of the primary Cs^+ ion current with 16 keV impact energy was quantified for the NanoSIMS-HR and a NanoSIMS 50L with the same Al-Si sample (Fig. 1 & S1; Table S2). For the NanoSIMS-HR tests, the primary current on the sample was set to values from ≤ 0.2 pA Cs^+ (below Faraday Cup detection limit) to 600 pA Cs^+ . The best lateral resolution for the NanoSIMS-HR Cs^+ source was 25 nm, compared to 45 nm for the 50L. The specifications are set to 30 nm and 50 nm, respectively. The NanoSIMS-HR resolution at 600 pA was ~ 600 nm, compared to 100 pA for similar resolution with the 50L. At 100 nm lateral resolution, the data show a 2.5-fold improvement in current density for the NanoSIMS-HR over the NanoSIMS 50L.

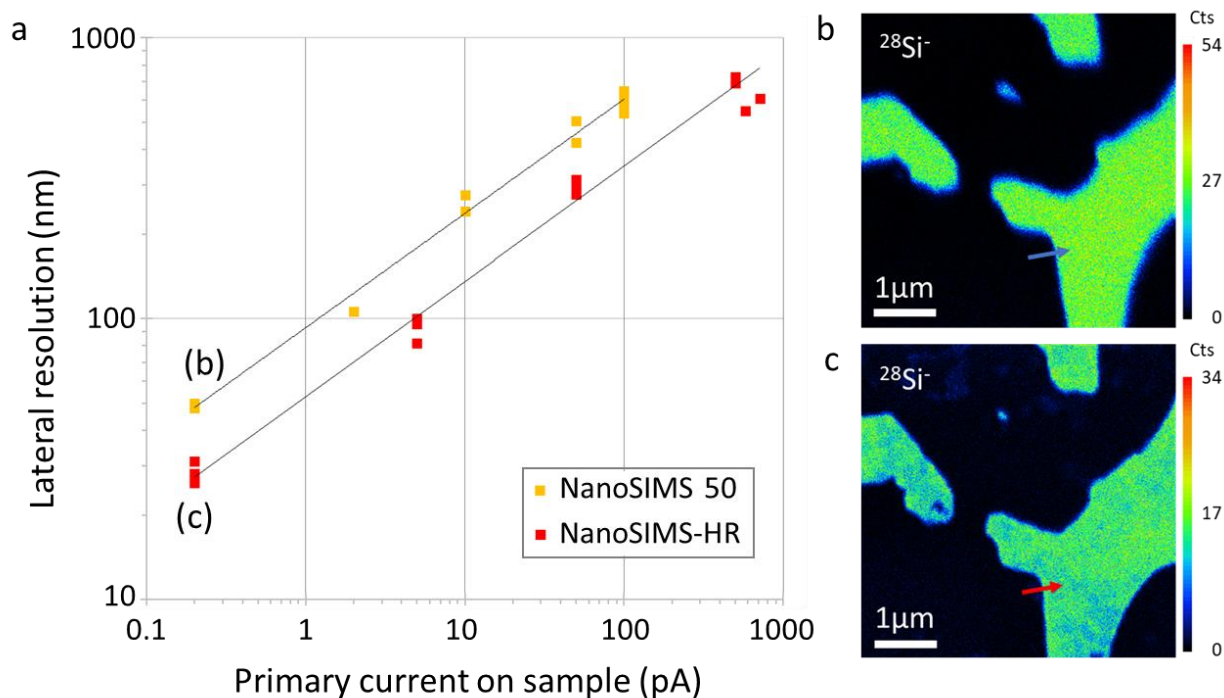


Figure 1. (a) Comparison of lateral resolution vs. Cs^+ primary current for the NanoSIMS 50L and the NanoSIMS-HR on an Al-Si sample. Correlated Al-Si sample images at the ultimate resolution (≤ 0.2 pA) for (b) a NanoSIMS 50L with ~ 45 nm lateral resolution and (c) the NanoSIMS-HR with ~ 25 nm lateral resolution. Arrows indicate example locations where lateral resolution was measured. The difference in ion counts (cts) per pixel is the result of different dwell times (1200 vs. 800 $\mu\text{s}/\text{pixel}$, respectively); the maximum $^{28}\text{Si}^-$ count rates were 43000 and 45000, respectively. See also Fig. S1.

We tested the improved lateral resolution of NanoSIMS-HR on a biological sample by imaging *P. tricornutum* algal cells with the ultimate resolution of the two instruments at 16 keV (Fig. 2). At ~ 30 nm lateral resolution, the ion images revealed small holes in the algal cell that would not be distinguishable with a standard NanoSIMS 50L, even at the ultimate resolution of 50 nm. These holes form during the sputtering of the *P. tricornutum* cell wall. We also tested the ability of the NanoSIMS-HR to deliver more current within a 100 nm spot. As expected, the secondary ion current increased 2.5x, proportional to the increase in current density.

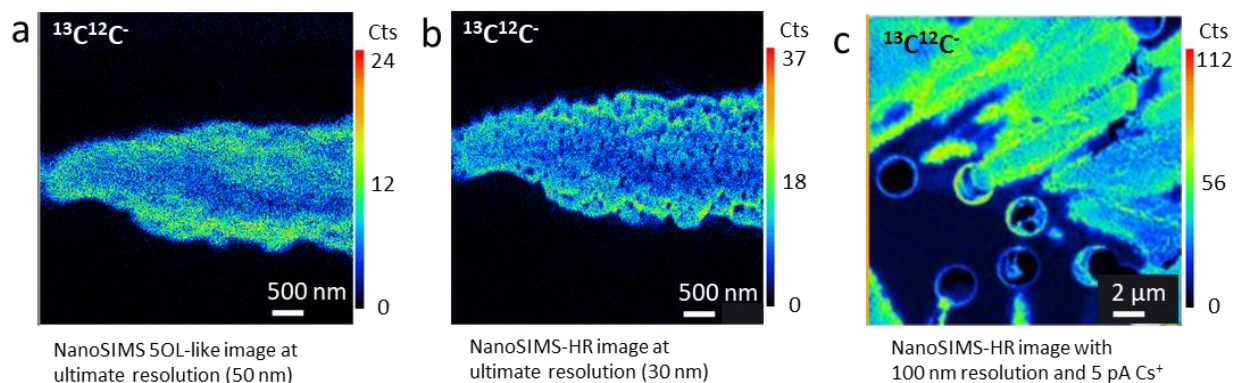


Figure 2. $^{13}\text{C}^{12}\text{C}^-$ ion images of the alga *P. tricornutum* show the difference in ultimate resolution for (a) NanoSIMS 50L and (b) NanoSIMS-HR. At 30 nm lateral resolution, small holes in the *P. tricornutum* cell can be clearly visualized with the NanoSIMS-HR, but not with a standard NanoSIMS 50L. (c) The NanoSIMS-HR can deliver $\sim 2.5\times$ current at 100 nm lateral resolution.

High-lateral-resolution NanoSIMS-HR analyses were also conducted on a 90-nm-thick section of a *P. hallii* root infected with *R. irregularis*, an arbuscular mycorrhizal fungus (Fig. 3 & S2). Figure 3 shows correlated TEM and NanoSIMS-HR $^{12}\text{C}^{14}\text{N}^-$ images of a subportion of an *R. irregularis* vesicle in the root tissue. The $^{12}\text{C}^{14}\text{N}^-$ image was collected with the 30 nm lateral resolution settings. The NanoSIMS-HR $^{12}\text{C}^{14}\text{N}^-$ image shows details that could be seen in the TEM image, as well as chemical contrast that could not. The TEM image shows sub-micron structures inside the vesicle that were visualized with the $^{12}\text{C}^{14}\text{N}^-$ ion in the NanoSIMS-HR, indicating that it was N-rich. The NanoSIMS-HR $^{12}\text{C}^{14}\text{N}^-$ image also shows that the vesicle wall is composed of multiple micron-scale layers of N-rich material. This material exhibited 100-nm-scale texture in the NanoSIMS-HR $^{12}\text{C}^{14}\text{N}^-$ image that is not visible in the TEM image, which we suspect was caused by extended ion bombardment.

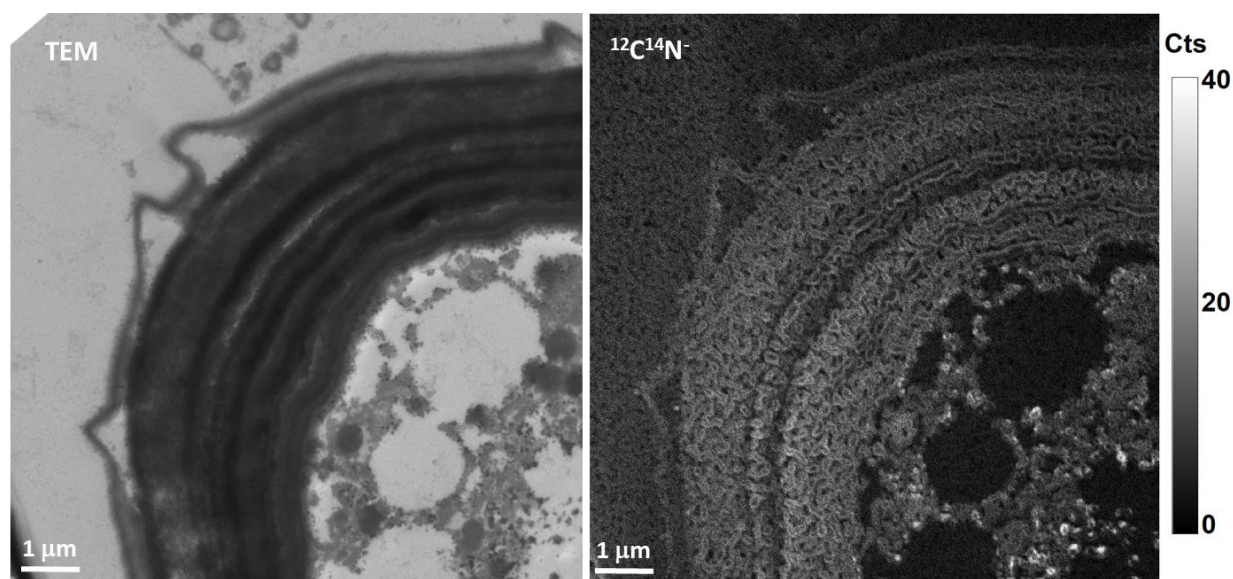


Figure 3. Correlated TEM and NanoSIMS-HR CN^- images of the multi-layer *R. irregularis* vesicle wall inside a *P. hallii* root. Implantation before data collection $\sim 3\times 10^{15} \text{ Cs}^+/\text{cm}^2$

Lateral and depth resolution with lower impact energy

The standard NanoSIMS impact energy of 16 keV is optimized to provide high lateral resolution and high transmission but is expected to result in worse depth resolution than lower impact energies as the primary ions penetrate deeper into the samples. We investigated this trade off with lateral and depth resolution measurements.

Lateral resolution was measured at 16, 8, 4, and 2 keV on the Al-Si sample. As expected, lateral resolution decreased with impact energy (Fig. 4 & S3). The degradation of lateral resolution between 16 keV and 2 keV was on the order of a factor of 5 to 10 depending on beam current.

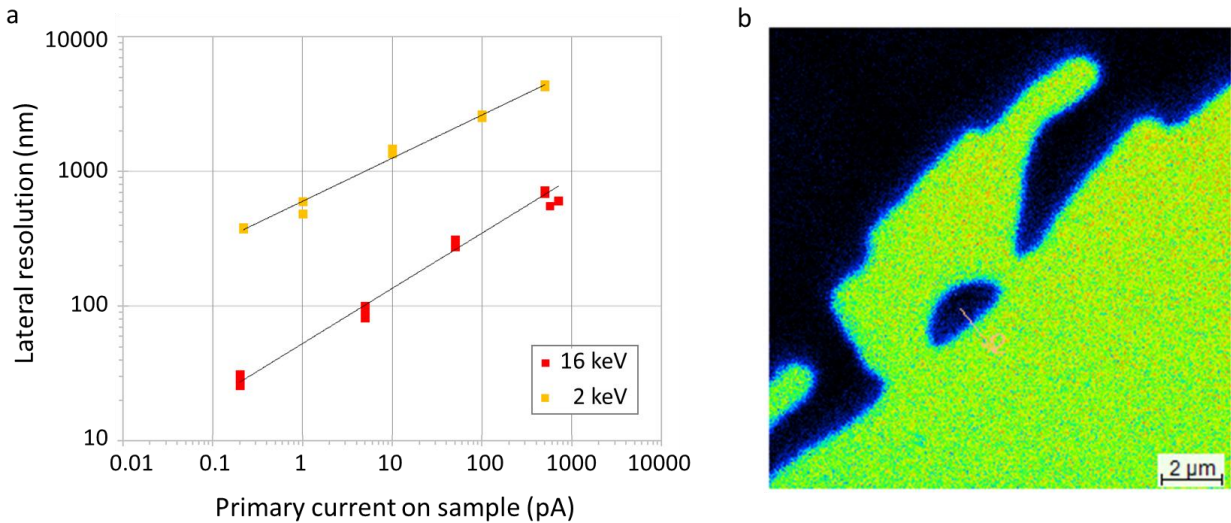


Figure 4. (a) Comparison of Cs^+ primary current vs. lateral resolution for the NanoSIMS-HR with 16 and 2 keV impact energy. (b) NanoSIMS-HR Si^- ion image of silicon grain in Al-Si sample using ≤ 0.2 pA Cs^+ at 2 keV with lateral resolution = 378 nm.

Depth resolution was measured on the trailing edge of P delta layers deposited on a silicon wafer (Fig. 5 and Table 1; see Methods for sample and measurement descriptions). The results are expressed as the depth in which the $^{31}\text{P}^-$ count rate declined by a decade (nm/decade). The depth resolutions for the two surface layers are not used because they are too close to the next deeper layer, resulting in $^{31}\text{P}^-$ counts from the deeper layer interfering with the measurement. Based on the two deeper layers, the depth resolution is ~ 22 nm/decade at the 16 keV impact energy, ~ 15 nm/decade at 8 keV and ~ 12 nm/decade at 4 keV.

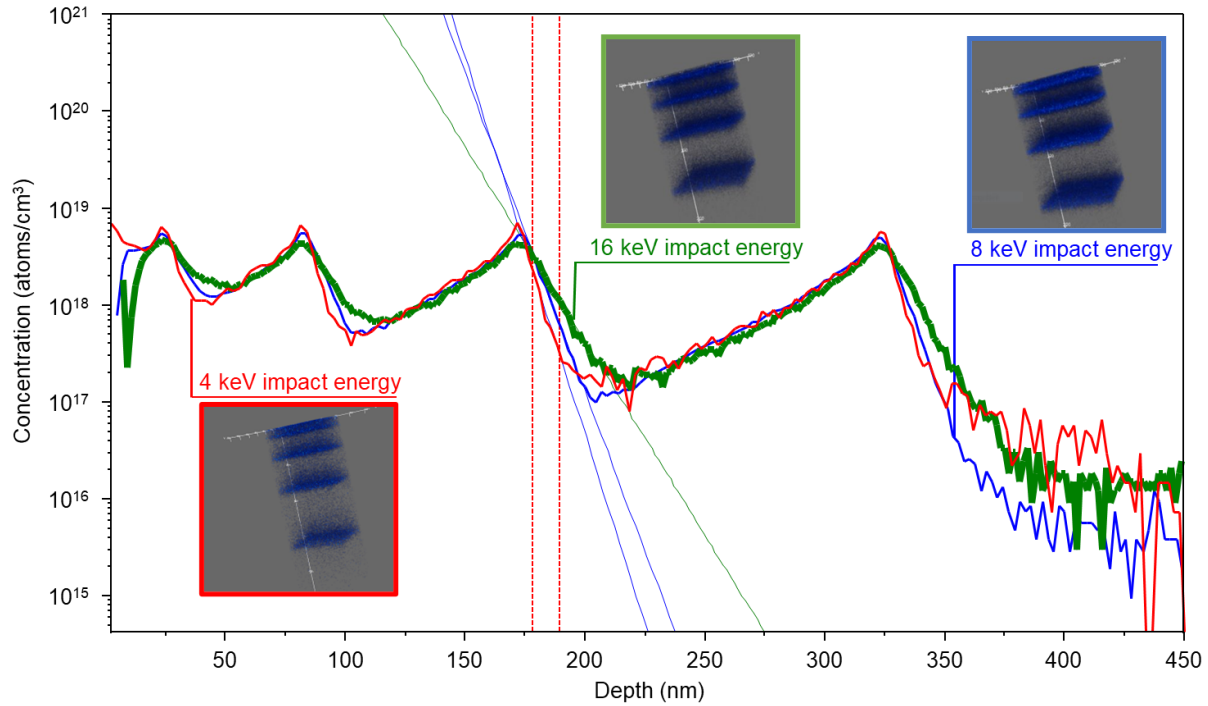


Figure 5. P depth profiles in a phosphorus-silicon delta layer sample with 16, 8 and 4 keV Cs⁺ impact energy. Inset images show 2D projections of the 3D distribution of the ³¹P⁻ ions detected with depth in the silicon matrix for the three profiles. Note that depth resolution is measured on the trailing edge of the P delta layer because it presents a sharp chemical contrast (see Experimental Section).

Table 1. Depth resolution as a function of primary impact energy.

	Depth resolution (nm/decade ³¹ P ⁻ counts)		
Delta layer	16keV	8keV	4keV
#1 (30nm)	34	20	14
#2 (90nm)	29	16	13
#3 (180nm)	22	15	12
#4 (330nm)	22	14	11

Detection limit for P

A Si wafer implanted with a known dose of P was used to determine the minimum P detection limit and corresponding minimum raster size and optimum ROI for a range of Cs⁺ primary ion currents (Fig. 6, S4 & S5). The detection limit for P improved from 10¹⁷ atoms per cubic centimeter (at./cm³) for 10 pA Cs⁺ with a 0.6 x 0.6 μm² ROI from a 2 x 2 μm² raster, to 10¹⁴ at./cm³ for 8 nA Cs⁺ with a 12 x 12 μm² ROI from a 40 x 40 μm² raster. We found a consistent relationship between detection limit, minimum raster size and relative ROI size (Fig. 6). The detection limit was lower for higher beam currents because of the larger dynamic range between the peak of the P implant and the tail, but the raster size had to be increased to obtain the minimum detection limit because the primary beam diameter increased with beam current³.

We found that the minimum raster size was approximately 20 to 30 times the beam diameter, and the optimum ROI was approximately 10% of the raster area (Fig. S5).

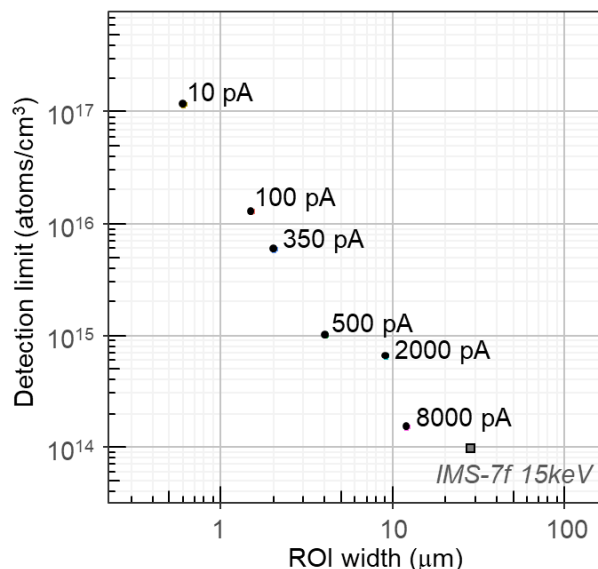


Figure 6. P detection limit for 10 to 8000 pA (16 keV) vs. ROI width. These ROIs are ~10% of the total raster size. The Cs⁺ current in pA is on the sample. IMS-7f data for comparison.

Stage reproducibility

The X and Y reproducibility of the sample stage was tested by moving the sample back and forth between the SIMS analysis position and the optical microscope and collecting an ion image eight times (Table 2). Shifts in the imaged feature are measured as pixel shifts and translated to nm based on the number of pixels per nm for the collected images. The observed reproducibility was ≤ 250 nm, which is well within the 500 nm specification.

Table 2. Stage movement reproducibility as measured by shift between images with image 1 as the reference.

Image number	Vertical shift (nm)	Horizontal shift (nm)
1	0	0
2	0	-94
3	235	47
4	282	71
5	235	212
6	141	118
7	424	-94
8	612	-118
1 SD	207	117

Isotopic ratios

No significant changes were made to the double focusing mass spectrometer part of the instrument, and therefore no change in isotopic ratio measurement performance was anticipated for the NanoSIMS-HR, and none was found (Table 3; Fig. S6). All measurements were within the precision specified for both instruments, and in this case, all but one had sub-permil precision (1σ). For the Si isotope measurements, high current analyses with Faraday cups achieved ~10x higher precision for the small (microns) and medium (millimeters) movement test, and ~2x higher precision for the large (10s of millimeters) movement test, relative to the lower current analyses with EMs. The O isotope measurements with Faraday cups and the electron flood gun (e-gun) also achieved sub-permil precision.

Table 3. Isotopic ratio measurement relative standard deviation (RSD). See Table S1 for test details.

Test	Specification (50L and HR)	RSD
A: $^{29}\text{Si}/^{28}\text{Si}$ and $^{30}\text{Si}/^{28}\text{Si}$ on silicon wafers using electron multipliers only	Test A1: RSD (1σ) ≤ 1.25 ‰ 10 analyses separated by 20 μm	0.63 ‰ $^{29}\text{Si}/^{28}\text{Si}$ 0.57 ‰ $^{30}\text{Si}/^{28}\text{Si}$
	Test A2: RSD (1σ) ≤ 1.40 ‰ 10 analyses, deflection mode within 35 x 35 μm^2 area	0.73 ‰ $^{29}\text{Si}/^{28}\text{Si}$ 0.93 ‰ $^{30}\text{Si}/^{28}\text{Si}$
	Test A3: RSD (1σ) ≤ 1.25 ‰ 16 analyses, stage moves across 8x8 mm^2 area	0.85 ‰ $^{29}\text{Si}/^{28}\text{Si}$ 0.91 ‰ $^{30}\text{Si}/^{28}\text{Si}$
	Test A4: RSD (1σ) ≤ 1.65 ‰ 12 analyses, 5 different samples	1.02 ‰ $^{29}\text{Si}/^{28}\text{Si}$ 0.80 ‰ $^{30}\text{Si}/^{28}\text{Si}$
B: $^{29}\text{Si}/^{28}\text{Si}$ and $^{30}\text{Si}/^{28}\text{Si}$ on silicon wafers using Faraday cups only	Test B1: RSD (1σ) ≤ 0.45 ‰ 10 10x10 μm^2 analyses separated by 20 μm	0.13 ‰ $^{29}\text{Si}/^{28}\text{Si}$ 0.06 ‰ $^{30}\text{Si}/^{28}\text{Si}$
	Test B2: RSD (1σ) ≤ 0.60 ‰ 16 10x10 μm^2 analyses across an 8x8 mm^2	0.08 ‰ $^{29}\text{Si}/^{28}\text{Si}$ 0.08 ‰ $^{30}\text{Si}/^{28}\text{Si}$
	Test B3: RSD (1σ) ≤ 0.80 ‰ 12 10x10 μm^2 analyses, 5 different samples	0.30 ‰ $^{29}\text{Si}/^{28}\text{Si}$ 0.56 ‰ $^{30}\text{Si}/^{28}\text{Si}$
C: $^{18}\text{O}/^{16}\text{O}$ on quartz using Faraday cups only	Test C1: RSD (1σ) ≤ 0.80 ‰ 10 10x10 μm^2 analyses separated by 20 μm	0.17 ‰ $^{18}\text{O}/^{16}\text{O}$
	Test C2: RSD (1σ) ≤ 1.00 ‰ 16 10x10 μm^2 analyses across an 8x8 mm^2	0.54 ‰ $^{18}\text{O}/^{16}\text{O}$

Discussion

Our tests on the newly redesigned CAMECA NanoSIMS, called the NanoSIMS-HR, demonstrate that features of the new instrument substantially improve imaging, depth profiling, detection limits and automated performance while maintaining secondary ion mass spectrometer performances, such as mass resolution, transmission, and isotope analyses presented here. The redesigned higher intensity thermal Cs^+ ion source is central to the improved performance, but other upgrades such as high-voltage control, an encoded sample stage, a higher resolution optical system, an automated sample exchange system, and new electronics further contribute to improved performance. The ion optics, secondary ion mass spectrometer and multicollection detector system are unchanged.

The redesigned, higher intensity Cs^+ ion source is a significant benefit of the NanoSIMS-HR. While the NanoSIMS 50 and 50L instruments had to meet the 50 nm lateral resolution specification, researchers have pushed to improve on this benchmark. Some researchers have reported better than 50 nm lateral resolution for the standard thermal Cs^+ ion source on NanoSIMS 50 series^{26,27}, but such performance would not be guaranteed by CAMECA. Others have sought to redesign the Cs^+ ion source to improve its intensity with some reported success^{14,15}, but no product is available yet for testing. Therefore, a reliable and commercially backed instrument that produces a 30 nm lateral resolution Cs^+ beam and overall higher Cs^+ current density is a significant advance for consumer access.

The ion images of biological samples in this study show the benefit of the improved lateral resolution. The NanoSIMS-HR was able to resolve finer features, such as the holes in the *P. tricornutum* cell wall (Fig. 2) and the structure of the contents of the AMF vesicle (Fig. 3). The relationship between imaging lateral resolution and analytical lateral resolution is somewhat complicated because it includes feature composition, feature spacing, analyte and analyte background²⁸, but in any case, improved resolution has benefits for navigation and feature identification. It is worth noting that although the highest resolution measurements in this study were made at low MRP to optimize the number of detected ions during a scan to achieve more accurate measurements of the analysis spot size, the same resolution scans could be made with higher MRP. For trace element and isotope analyses, multiple scans are typically made of an analysis area to accumulate statistically meaningful counts of the minor species.

While “ultimate resolution” is the featured specification, the higher current density benefits all analyses by enabling faster analyses, improving low impact energy imaging depth profiling, and lowering detection limits. For example, bacterial analyses with 100 nm lateral resolution can be performed at least 2.5 times faster with the NanoSIMS-HR (5 pA vs. 2 pA for 50L; Fig. 1 & 2). The majority of published papers do not use the ultimate resolution of the NanoSIMS 50 or 50L but rather a lower-resolution, higher-current primary ion beam setting that allows faster analyses, lower detection limits, and generally more straight forward operation. One notable point is that secondary electron imaging, which can be used with the Cs^+ ion source for navigation and feature identification, can be very poor at the very low primary current setting (~0.2 pA) necessary to achieve the ultimate resolution.

The ability to vary the NanoSIMS-HR source and sample high voltage from 8 keV down to 1 keV allows the user to trade off lateral resolution for depth resolution. Our results show that at 4 keV impact energy (2 keV on source, -2 keV on the sample), there is an approximately 2-fold improvement in depth resolution with an approximately 5-fold loss in lateral resolution. While the actual lateral resolution is better than it would have been with the previous thermal Cs^+ source, the source intensity is still affected

by reducing the source high voltage because it extracts the electrons that heat the source, and the ability of the electronics to compensate has limits.

We tested the P detection limit with 10 to 8000 pA Cs⁺ primary beam current. The improvement in the detection limit with higher beam current reflects the increase in the dynamic range between the implanted P and the background³. The relationship between beam current and detection limit in the P analyses in this study reflects an optimal relationship between the primary current resolution, the sputtered area and the target area for data extraction (Fig. 6). We found that the optimum relationship between primary beam diameter and raster size was a factor of 20 to 30. Smaller rasters result in significant contribution of P⁻ counts from the periphery of the analysis crater to the central ROI. We also found that the optimal ROI size is ~10% of the raster size; smaller ROIs result in a reduced dynamic range and limitation on the number of atoms in the analyzed area (Fig. S5). We do not have comparable 50L data, but we would expect the ROI for any given detection limit to be larger because of the lower beam intensity. Based on previous work, the minimum size that a feature of interest could be is the size of the ROI plus two beam widths³.

Higher primary beam current density also lowers background for analyses such as H and O, where the background count rate is proportional to the rate at which these species in the analysis chamber vacuum interact with the sample surface²⁹. Higher spatial resolution also increases sensitivity to the composition of the target feature by sampling the feature and not the adjacent material.

The improved stage control can further speed up automated analyses by allowing the primary beam raster to be more tightly framed on a series of preselected targets, such as cells or particles. The analysis area has to be scaled based on the stage precision to ensure that selected targets are hit. The proportional increase in area directly translates to analysis time to collect sufficient ions from the target. The greatest improvement is for small targets (e.g., 1 μm ϕ), where the increase in analysis speed would be between 30 and 100 times, depending on whether one allows for 5- or 10-micron stage reproducibility with a NanoSIMS 50L (analysis time is proportional to the square of the target size + 2x stage reproducibility; Fig. S7). For larger targets, the increase in analysis speed reduces geometrically down to 2 to 3 times for 30-micron diameter targets, which is still a significant time savings.

Conclusion

The NanoSIMS-HR provides improved spatial resolution, detection limits, and throughput compared to its predecessors, the NanoSIMS 50 and 50L. The improved thermal Cs⁺ ion source is central to the improved performance of the NanoSIMS-HR, while features like HV control, improved navigation, and a precision stage also provide significant benefits.

Acknowledgements

We thank the reviewers for detailed reviews that greatly improved this manuscript. Primary funding for this research was provided by U.S. Department of Energy (DOE) Office of Biological and Environmental Research (BER) award SCW1039. Support to JPR was provided by DOE BER award SCW1632, and support to RH was provided by the Foundation for Food & Agriculture Research under award number 23-000585. Instrumentation funding was provided by DOE BER and Lawrence Livermore National Laboratory (LLNL). Research at LLNL was performed under the auspices of DOE under Contract DE-AC52-07NA27344.

Supporting Information

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Fig. S5. P detection limit versus ROI size for individual analyses.

Fig. S6. Isotope measurement plots for the nine specification tests.

Fig. S7. Relative analysis time factor as a function of target size for the NanoSIMS 50L vs. NanoSIMS-HR.

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Supplementary Information for:

The NanoSIMS-HR: the next generation of high spatial resolution dynamic SIMS

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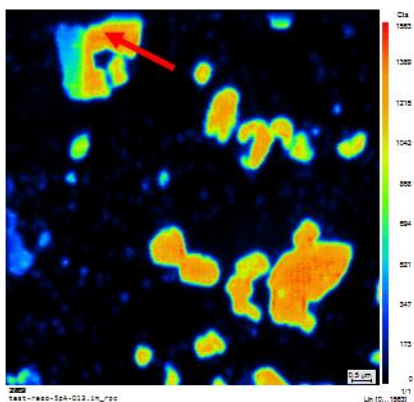
Table S1. CAMECA NanoSIMS-HR and 50L tests and specifications for isotope measurements.

- A1. $\delta^{30}\text{Si}$ and $\delta^{29}\text{Si}$ reproducibility with 3-EM configuration is under 1.25‰ (1 S.D.) on 10 measurements with internal precision (from Poisson statistic) $\leq 0.7\text{‰}$ (1.S.D.)
- A2. $\delta^{30}\text{Si}$ and $\delta^{29}\text{Si}$ reproducibility with 3-EM configuration reproducibility is $\leq 1.40\text{‰}$ (1S.D.) for a small area of $35 \times 35 \mu\text{m}^2$ in beam deflection mode. 2 measurements in each of the locations: center, N, S, E, W and center with ^{30}Si each with precision $\leq 0.7\text{‰}$ (1 S.D.) to demonstrate internal raster isotopic homogeneity
- A3. $\delta^{30}\text{Si}$ and $\delta^{29}\text{Si}$ reproducibility with 3-EM configuration is $\leq 1.25\text{‰}$ (1 S.D.) on 16 raster measurements distributed in an $8 \times 8 \text{ mm}^2$ square each with internal precision $\leq 0.7\text{‰}$
- A4. $\delta^{30}\text{Si}$ and $\delta^{29}\text{Si}$ reproducibility with 3-EM configuration on whole sample holder is $\leq 1.65\text{‰}$ (1 S.D.) on 12 measurements with internal precision $\leq 0.7\text{‰}$ 1 series of 2 measurements on 5 different Si wafers in the same sample holder are performed, ending on 2 measurement on the starting one wafer.
- B1. $\delta^{30}\text{Si}$ and $\delta^{29}\text{Si}$ reproducibility with 3-FC configuration Linear chained analysis reproducibility $\leq 0.45\text{‰}$ (1 S.D.) on 10 craters of $10 \times 10 \mu\text{m}^2$ separated by $20 \mu\text{m}$
- B2. $\delta^{30}\text{Si}$ and $\delta^{29}\text{Si}$ reproducibility with 3-FC configuration reproducibility $\leq 0.6\text{‰}$ (1 S.D.) in chained analysis of 16 craters of $10 \times 10 \mu\text{m}^2$ in an $8 \times 8 \text{ mm}^2$ square
- B3. $\delta^{30}\text{Si}$ and $\delta^{29}\text{Si}$ Full FC Square chained analysis reproducibility $\leq 0.80\text{‰}$ (1 S.D.) on 5 different samples of a sample-holder, 12 measurements of $10 \times 10 \mu\text{m}^2$
- C1. $\delta^{18}\text{O}$ reproducibility with FC/FC configuration $\leq 0.80\text{‰}$ (1 S.D.) on 10 craters of $10 \times 10 \mu\text{m}^2$ separated by $20 \mu\text{m}$
- C2. $\delta^{18}\text{O}$ reproducibility with FC/FC configuration $\leq 1.0\text{‰}$ on 16 different craters of $10 \times 10 \mu\text{m}^2$ inside a square of 8 mm (1-inch sample size).

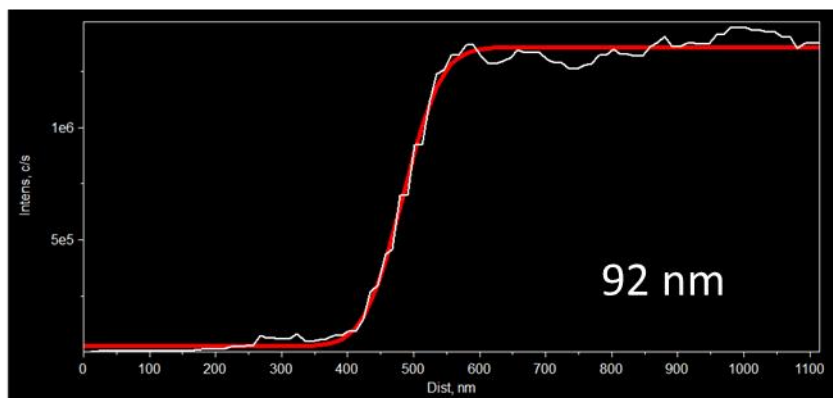
Table S2. CAMECA NanoSIMS-HR lateral resolution specifications.

FCo	D1	L1	resolution (NS-HR)
5 pA	3	~1200 V	100 (specification)
< 0.2 pA	5	8500 - 9000 V	30 (specification)

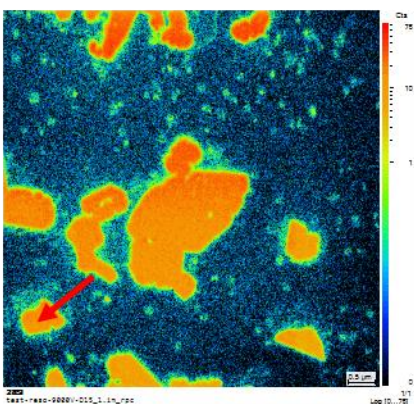
a



px. size: 20 nm



b



px. size: 14 nm

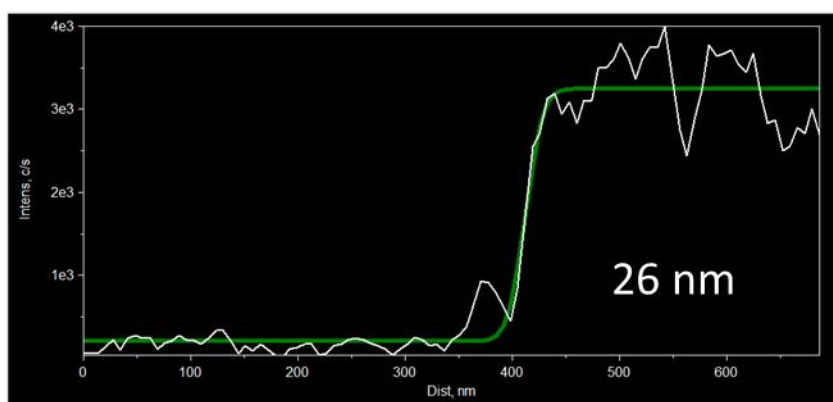


Fig. S1. Examples of lateral resolution measurements at 16 keV impact energy. ^{28}Si images, the line profile (arrows), the plotted data and the modeled resolution for (a) 5 pA and (b) 0.2 pA Cs^+ .

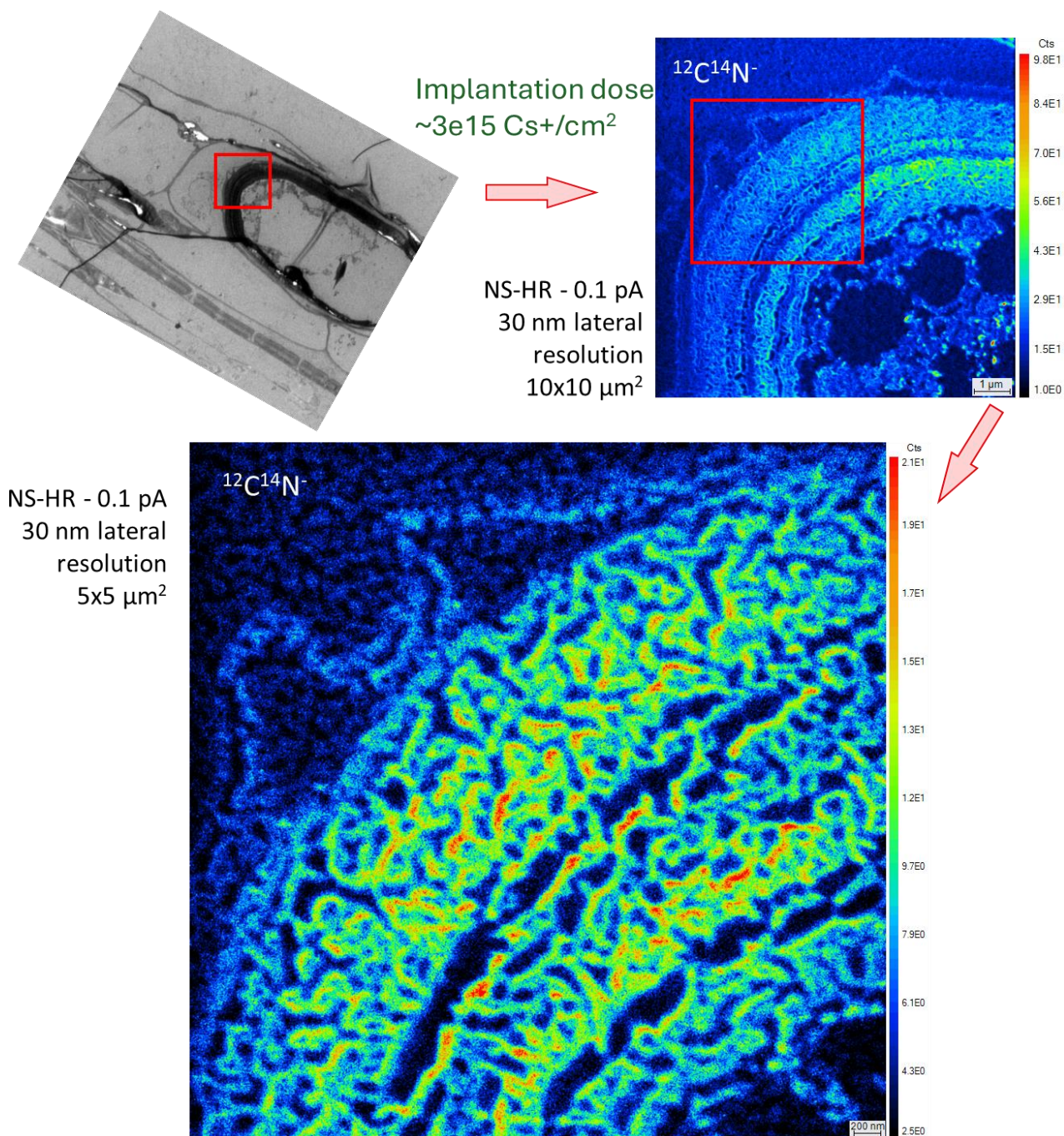


Fig. S2. Correlated TEM and NanoSIMS-HR CN^- images of an AMF vesicle in a *P. hallii* root at 16 keV impact energy. The images were collected in sequence. Boxes show the area of the subsequent image.

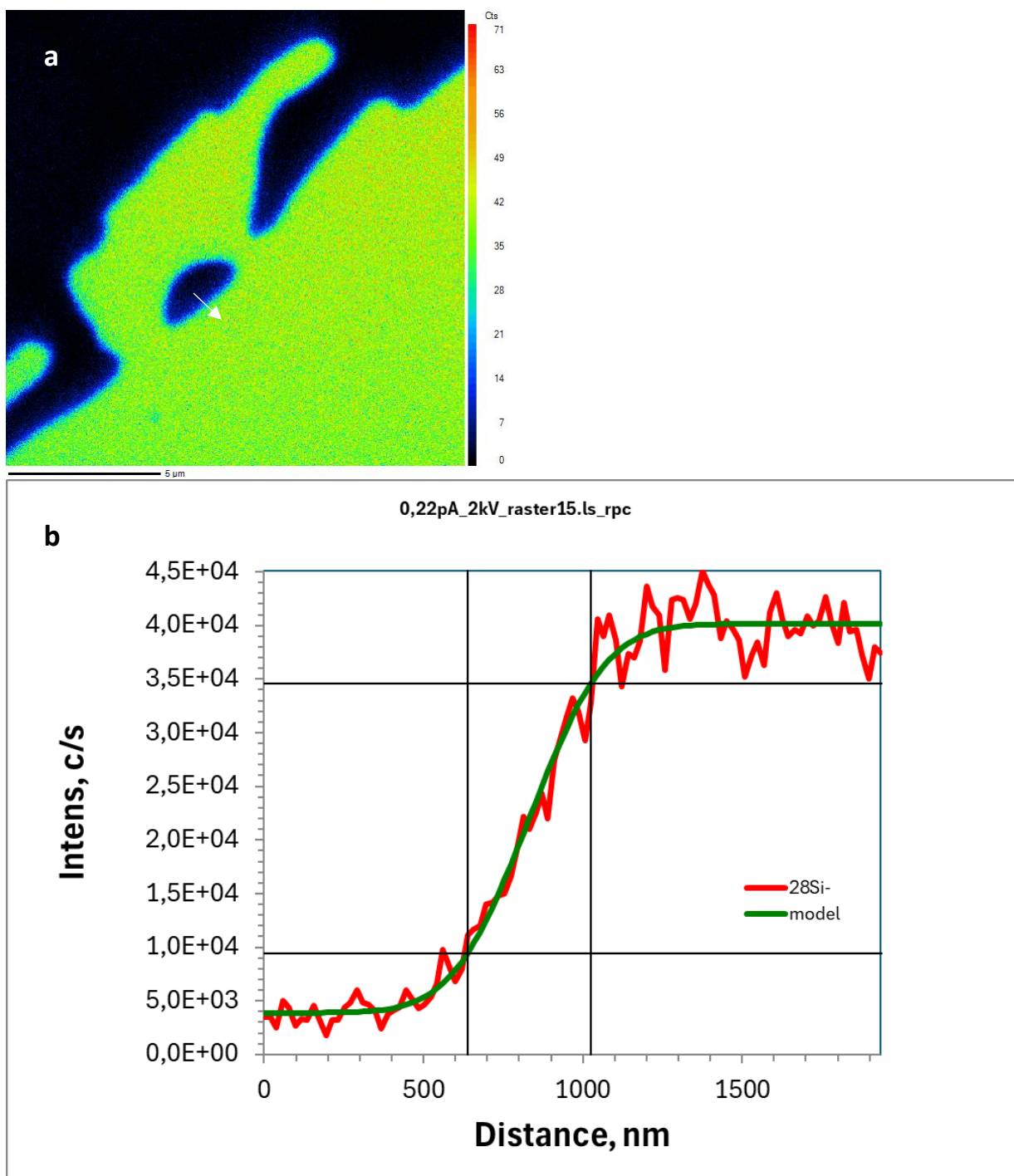
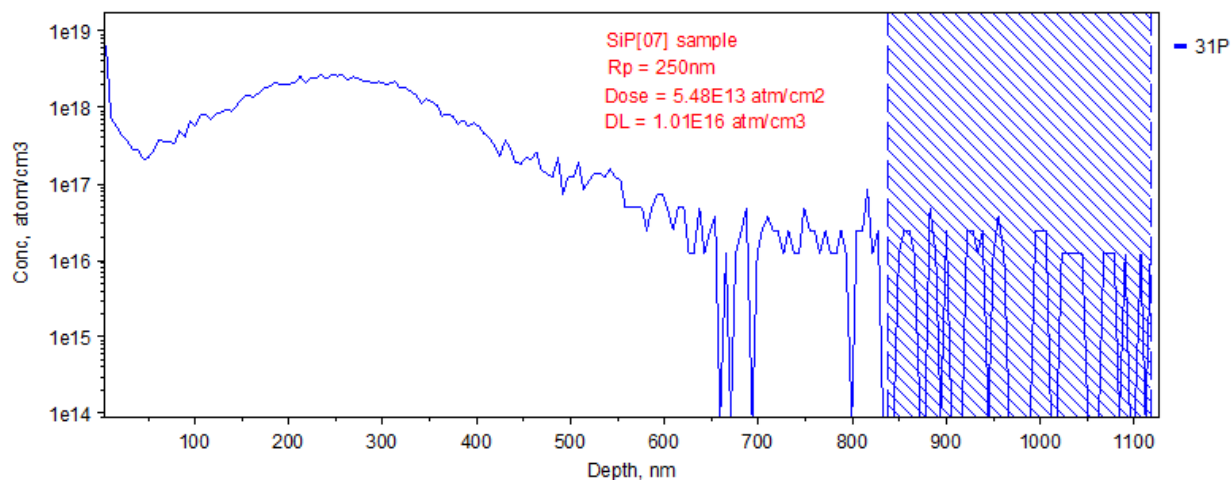


Fig. S3. Resolution at low impact energy. (a) $^{28}\text{Si}^-$ image collected with 0.2 pA Cs^+ with 2 keV impact energy, and (b) the measured lateral resolution for on an Al-Si sample (arrow in image center). The image is $15 \times 15 \mu\text{m}^2$ and was collected with 512×512 pixels.

100 pA Cs⁺



8000 pA Cs⁺

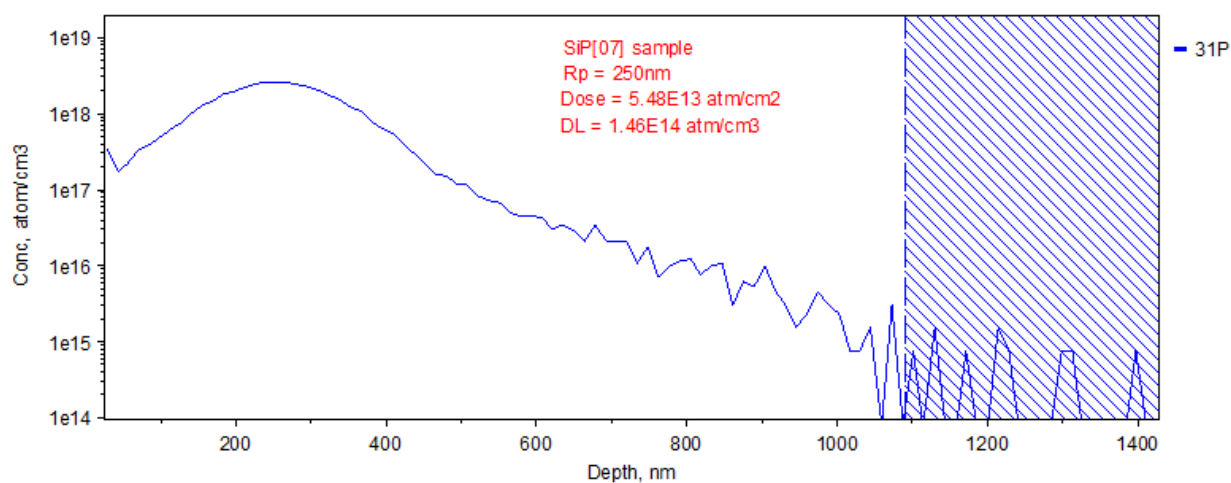


Fig. S4. Comparison of P depth profiles and detection limits for 100 versus 8000 pA Cs⁺. The analyses were made in the same silicon wafer implanted with P (dose = 5.45×10^{13} atoms/cm²). ³¹P counts are converted to P concentration based on the known P dose, and the detection limit is defined as the apparent concentration after sputtering through the P implant (shaded areas in the graphs). Note the difference in the apparent background P concentration due to the higher sputter rate resulting in lower detector background for the 8000 pA Cs⁺ depth profile, which translates to the lower detection limit.

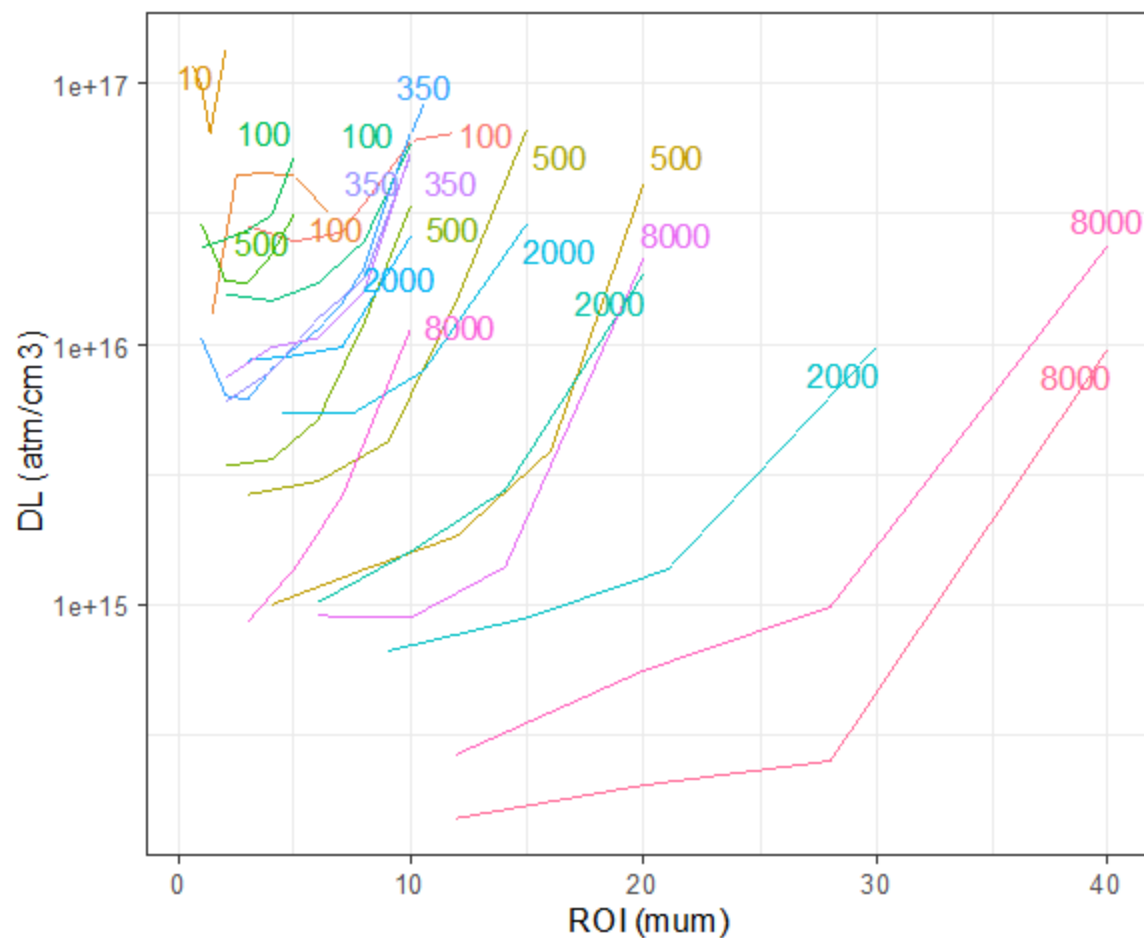
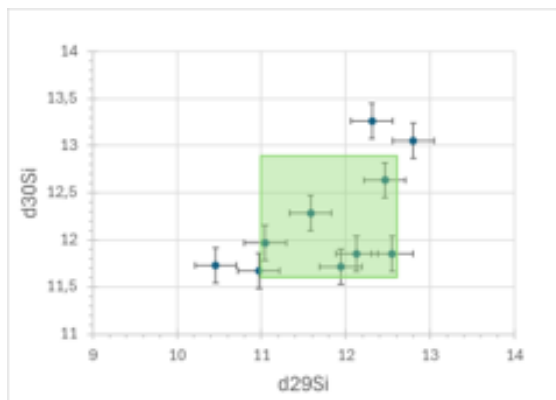
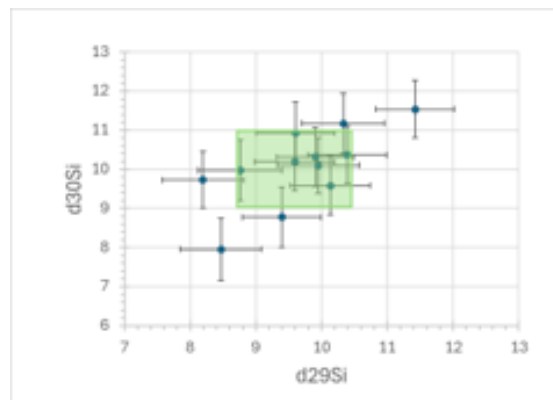


Fig. S5. P detection limit versus ROI size for individual analyses. The number associated with the individual curves is the Cs^+ primary ion current used for each measurement in pA. The raster size that resulted in the lowest detection limit for each primary current was tested empirically.

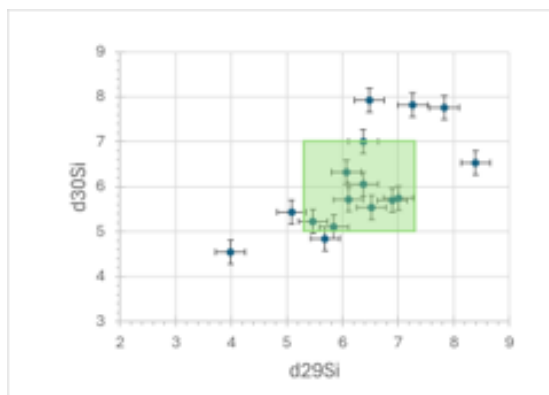
Fig. S6 (below). Isotope measurement plots for the nine specification tests. The shaded box in each graph represents the ± 1 sigma results for the plotted data. See Table S1 for descriptions of the tests.



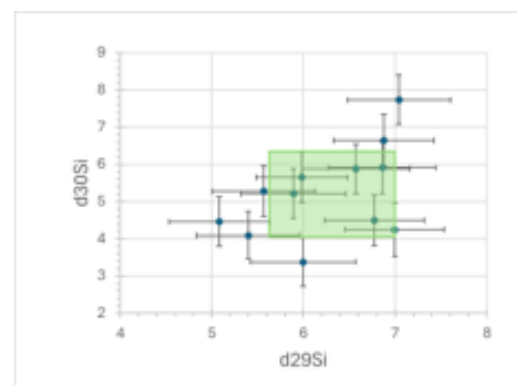
TEST A1, $\delta^{29}\text{Si}$ and $\delta^{30}\text{Si}$ $\sigma < 1.25$ ‰



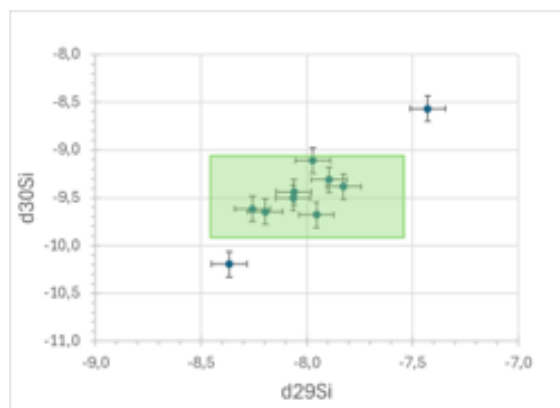
TEST A2, $\delta^{29}\text{Si}$ and $\delta^{30}\text{Si}$ $\sigma < 1.4$ ‰



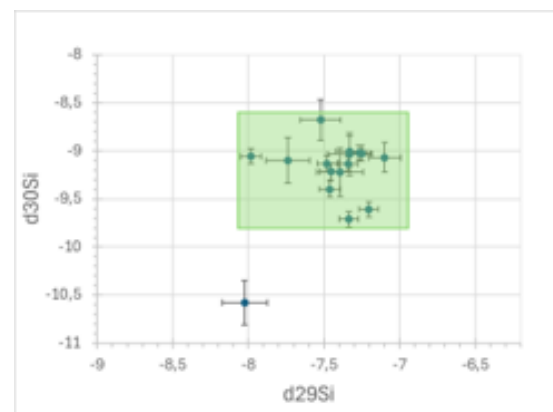
TEST A3, $\delta^{29}\text{Si}$ and $\delta^{30}\text{Si}$ $\sigma < 1.25$ ‰



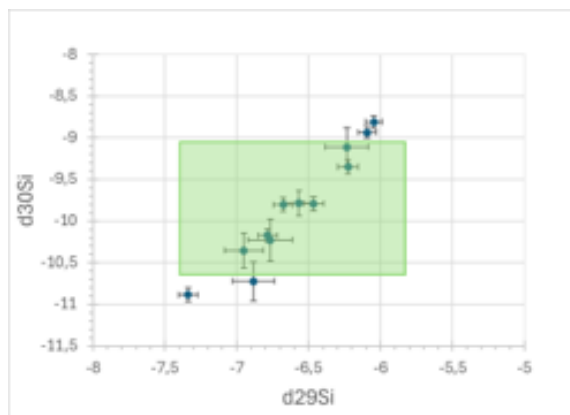
TEST A4, $\delta^{29}\text{Si}$ and $\delta^{30}\text{Si}$ $\sigma < 1.65$ ‰



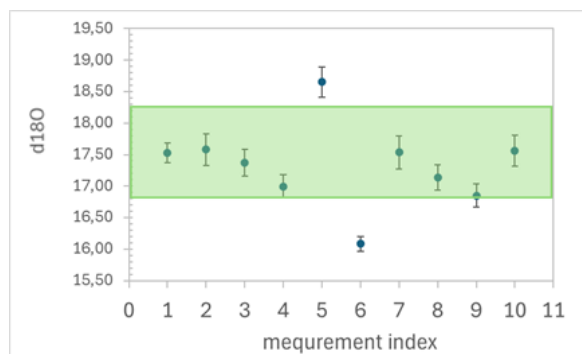
TEST B1, $\delta^{29}\text{Si}$ and $\delta^{30}\text{Si}$ $\sigma < 0.45$ ‰



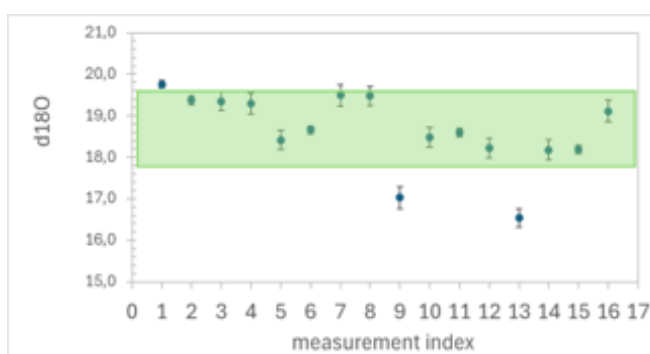
TEST B2, $\delta^{29}\text{Si}$ and $\delta^{30}\text{Si}$ $\sigma < 0.6$ ‰



TEST B3, $\delta^{29}\text{Si}$ and $\delta^{30}\text{Si}$ $\sigma < 0.8\text{‰}$



TEST C1, $\delta^{18}\text{O}$ $\sigma < 0.8\text{‰}$



TEST C2, $\delta^{18}\text{O}$ $\sigma < 1.0\text{‰}$

END FIG. S6.

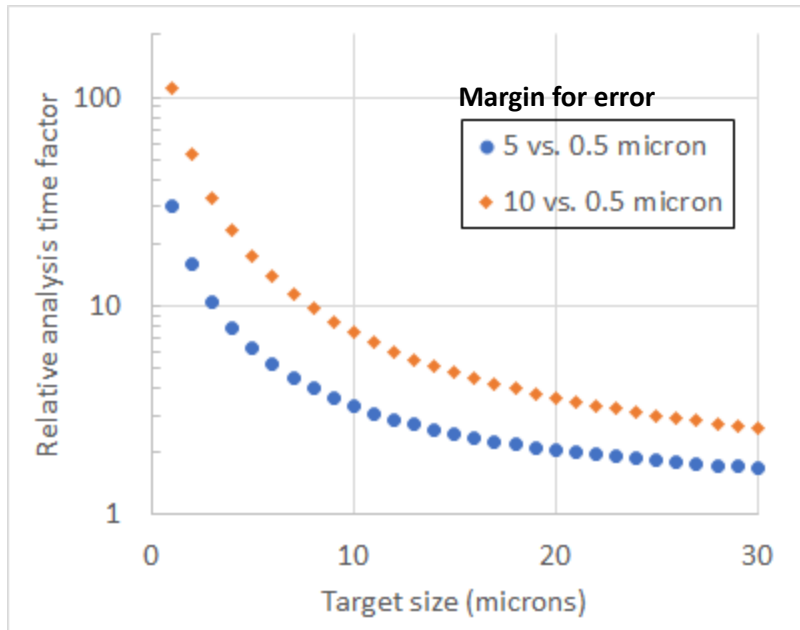


Fig. S7. Relative analysis time factor as a function of target size for the NanoSIMS 50L vs. NanoSIMS-HR. The relative analysis time factor is the ratio of the time necessary for the NanoSIMS 50L relative to the NanoSIMS-HR to collect the same number of ions from a targeted feature accounting for the size of the raster necessary to ensure hitting the targeted feature with automated stage movements. The margin for error is defined as the reproducibility of the sample stage, which is <0.5 microns for the NanoSIMS-HR and between 5 and 10 microns for the NanoSIMS 50L. The larger the margin for error, the larger the analysis size needs to be to hit the targeted feature, increasing the analysis time geometrically. The graph compares 5- vs 0.5-micron margin for error and 10- vs 0.5-micron margin for error. The curves are based on the following equation:

$$RAT = (X_t + 2 * MFE_{50})^2 / (X_t + 2 * MFE_{HR})^2$$

Where RAT is the relative analysis time factor, X_t is the lateral width of a targeted symmetric feature, and MFE_x is the margin for error for the 50 and 50L series and the HR.